

Application No. 10/043,534

Reply to Office Action

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## AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions, and listings, of claims in the application.

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1. (Currently Amended) A system for polishing a substrate ~~comprising~~ consisting essentially of (i) a liquid carrier, (ii) ammonium oxalate, (iii) a hydroxy coupling agent, (iv) fumed silica, (v) a film-forming agent, and ~~(v)~~ (vi) a polishing pad, wherein the system does not comprise an oxidizing agent, ~~and wherein the polishing system has a pH of about 8-12.~~
2. (Original) The polishing system of claim 1, wherein the liquid carrier is a nonaqueous solvent.
3. (Original) The polishing system of claim 1, wherein the liquid carrier is water.
4. (Canceled)
5. (Previously Presented) The polishing system of claim 3, wherein the fumed silica is fixed on the polishing pad.
6. (Previously Presented) The polishing system of claim 3, wherein the fumed silica is suspended in the water.
7. (Canceled)
8. (Canceled)
9. (Previously Presented) The polishing system of claim 6, wherein the hydroxy coupling agent is ureidopropyltrimethoxysilane.
10. (Canceled)
11. (Currently Amended) The polishing system of claim ~~6~~ 1, wherein the film-forming agent is an organic heterocycle comprising at least one 5-6 member heterocyclic nitrogen-containing ring.
12. (Original) The polishing system of claim 11, wherein the film-forming agent is benzotriazole.

Application No. 10/043,534

Reply to Office Action

13. (Original) The polishing system of claim 3, wherein the hydroxy coupling agent is a silane-containing compound.
14. (Original) The polishing system of claim 13, wherein the hydroxy coupling agent is ureidopropyltrimethoxysilane.
15. (Original) The polishing system of claim 3, wherein the pH is about 9-11.
16. (Original) A method of polishing a substrate comprising contacting at least a portion of a substrate with the polishing system of claim 1 and polishing the portion of the substrate therewith.
17. (Original) The method of claim 16, wherein the substrate comprises copper.
18. (Original) The method of claim 17, wherein the substrate further comprises tantalum.
19. (Original) The method of claim 18, wherein the Cu:Ta removal rate is at least about 1:1.
20. (Original) The method of claim 17, wherein the substrate further comprises tetraethoxysilane.
21. (Original) The method of claim 20, wherein the Cu:TEOS removal rate is at least about 1:2.
22. (Original) A method of polishing a substrate comprising contacting at least a portion of a substrate with the polishing system of claim 12 and polishing the portion of the substrate therewith.
23. (Original) The method of claim 22, wherein the substrate comprises copper.
24. (Original) The method of claim 23, wherein the substrate further comprises tantalum.
25. (Original) The method of claim 24, wherein the Cu:Ta removal rate is at least about 1:1.
26. (Original) The method of claim 23, wherein the substrate further comprises tetraethoxysilane.

Application No. 10/043,534

Reply to Office Action

27. (Original) The method of claim 26, wherein the Cu:TEOS removal rate is at least about 1:2.